Contents lists available at SciVerse ScienceDirect



Journal of Magnetism and Magnetic Materials



journal homepage: www.elsevier.com/locate/jmmm

Structural, electronic and magnetic properties of $Fe_{3-x}Mn_xZ$ (Z=Al, Ge, Sb) Heusler alloys

Said M. Azar, Bothina A. Hamad, Jamil M. Khalifeh*

Department of Physics, University of Jordan, Amman 11942, Jordan

ARTICLE INFO

ABSTRACT

Article history: Received 25 July 2011 Received in revised form 9 December 2011 Available online 17 January 2012

Keywords: Heusler alloy Half-metal DFT First principle FP-LAPW Magnetism Spin gap Density functional theory based on full-potential linearized augmented plane-wave (FP-LAPW) method is used to investigate the structural, electronic and magnetic properties of $Fe_{3-x}Mn_xZ$ (Z=Al, Ge, Sb) Heusler alloys, where $0 \le x \le 3$. Alloys with $x \le 1$ are found to exhibit a ferromagnetic phase, whereas the rest have shown ferrimagnetic phase. The total spin magnetic moment shows a trend consistent with generalized Slater–Pauling type behavior. Alloys with x > 0.75 are found to be half metallic with indirect band gaps along $\Gamma - X$ symmetry line for stoichiometric and direct band gaps for nonstoichiometric alloys. We found that Mn rich composition of $Fe_{3-x}Mn_xZ$ alloys has high spin polarization. © 2012 Elsevier B.V. All rights reserved.

1. Introduction

Recently, functional materials such as Heusler alloys [1] have attracted attention in fundamental and engineering science because of their new possible applications and phenomena. Heusler alloys have been the subject of experimental and theoretical interests due to three unique properties. Firstly, half-metallic behavior [2], where the majority spin band usually shows typical metallic behavior, whereas the other spin band (usually minority spin) is semiconducting or insulating, with fully spin polarization at Fermi level. Secondly, magnetic shape memory effect [3], where the magnetic shape memory alloys undergo structural transformations by changing the magnetic field. Thirdly, the inverse magnetocaloric effect [4], where some magnetic materials possess a reversible change in temperature caused by exposing the material to a changing magnetic field.

In addition to these three unique properties, Heusler alloys also provide fundamental aspects for magnetism in complex systems. Electronic structure calculations from first principles have been extensively used to predict new materials with predefined properties in order to maximize the efficiency of devices. Novel materials for spintronics applications have especially attracted considerable interest in the last decade [5]. Moreover, there has been an upsurge of interest in the ordered compound containing Fe. Furthermore, Heusler alloys of the type Fe_2MnZ [6] and Mn_2FeZ [7] have been proposed theoretically to show half-metallicity. Intermetallic Heusler alloys are amongst the most attractive half-metallic systems due to the high Curie temperatures, low coercivities, and the structural similarity to the binary semiconductors such as GaAs.

Concerning relevant theoretical studies, there is a substantial literature devoted to a variety of ordered Heusler-type phases and related systems where many previous studies are concerned to explain the effect of impurities concentration on the structural and magnetic properties of Heusler alloys. An extensive review of $Fe_{3-x}T_xSi$ alloys for various transition metals (T) has been carried out by Niculescu et al. [8]. Pugaczowa-Michalska et al. [9] examined the effect of local environment on the formation of local magnetic moments of Fe_{3-x}Mn_xAl alloys in the concentration range $0 \le x \le 0.5$. In a recent work [10] we studied theoretically the electronic structure and spin polarization of Fe_{3-x}Mn_xSi and Fe_{3-v}MnSi_v alloys and found that the half-metallic behavior starts at x = 0.75 with a small direct band gap that increases for higher Mn concentrations. In addition, we investigated the electronic and magnetic properties of Fe_{3-x}Cr_xSi alloys, by adopting two phases as the parent structures Fe₃Si and Fe₃Si have different phases, namely the L2₁ and A15, respectively [11]. We found that the alloys with Cr concentration of $x \le 0.75$ are more stable with the L2₁ than the A15 phase and vice versa for higher Cr concentrations.

The goal of this research work is to study, with ab initio accuracy over a wide concentration range, the effect of the main-group

^{*} Corresponding author.

E-mail address: jkalifa@ju.edu.jo (J.M. Khalifeh).

^{0304-8853/\$ -} see front matter © 2012 Elsevier B.V. All rights reserved. doi:10.1016/j.jmmm.2011.12.037

elements on the electronic and magnetic structures of bulk $Fe_{3-x}Mn_xZ$ (Z=Al, Ge, Sb) stoichiometric series alloys. Manganese concentration and the main-group elements (Z) play an important role in the electronic and magnetic structures of these alloys. The influence of Mn concentration and main-group elements on the electronic and magnetic structures is discussed in this work. Furthermore, the half-metallic behavior is investigated for some alloys in the series. We are thus able to delineate clearly how the majority and minority spin states and magnetic moments in Fe₃Ge develop when the Fe[B] site in the lattice is substituted by Mn atoms, and/or when Ge is replaced by a metalloid of a different valence.

The rest of the paper is arranged as follows: Section 2 includes the structural details and the method of calculation, Section 3 is devoted to the results and discussion and Section 4 is a summary of our conclusions.

2. Computational details

Density functional theory (DFT) [12], using the all-electron full-potential linearized augmented plane-wave (FP-LAPW)

Table 1

Comparison between the present work and tabulated experimental values as well as previous calculations. Optimized lattice constant a (Å), bulk modulus B (GPa), maximum valence electron band energy ($E_{V(max)}$), minimum conduction electron band energy ($E_{C(min)}$), band gap (E_g), half-metallic (HM) gap (E_s) and polarization (P).

Compound	Structure	Pa (Å)	B (GPa)	$E_{V(max)}$ (eV)	$E_{C(min)}$ (eV)	E_g (eV)	E_S (eV)	P (%)
Fe ₃ Al	DO ₃	5.750	169.9					35
		5.738 ^a 5.820 ^b (<i>exp</i>)	169.3ª					
	L1 ₂	3.653	169.4					
		3.651 ^a	174.9 ^a					
Fe ₂ MnAl	L2 ₁ (Fm-3m)	5.683 5.670 ^c 5.850 ^d (<i>exp</i>)	200.9	0.740	1.205	0.465		81
Mn ₂ FeAl	L2 ₁ (F-43m)	5.760 5.725 ^e	150.2	0.674	1.218	0.544		99
Mn ₃ Al	DO ₃	5.806 5.723 ^f	143.9	0.555	1.098	0.543	0.116	100
Fe₃Ge	DO ₃	5.736 5.760 ^g (<i>exp</i>)	167.7					20
	L1 ₂	3.642 3.667 ^g (<i>exp</i>)	179.6					
Fe ₂ MnGe	L2 ₁ (Fm-3m) DO ₃	5.703 5.780 ^h (<i>exp</i>)	217.6	0.845	1.392	0.547		96
Mn ₂ FeGe	L2 ₁ (F-43m)	5.718 5.675 ^e	214.4	0.893	1.376	0.482		87
Mn₃Ge	DO ₃	5.765 5.749 ^f	197.2	0.828	1.326	0.497		96
	L1 ₂	3.654 3.800 ⁱ (<i>exp</i>)	170.5					
Fe₃Sb	DO ₃	5.996 5.90 ^b (<i>exp</i>)	159.5					23
Fe ₂ MnSb	L2 ₁ (Fm-3m)	5.955	192.6	0.979	1.668	0.689		82
Mn ₂ FeSb	L2 ₁ (F-43m)	5.999 5.925°	141.2	0.731	1.127	0.396	0.063	100
Mn₃Sb	DO ₃	5.985 5.930 ^f	174.4	0.768	1.375	0.607	0.043	100
	L1 ₂	3.811 4.000 ^j (<i>exp</i>)	177.1					

^a Ref. [28].

^b Ref. [29]. ^c Ref. [30].

^d Ref. [31].

^e Ref. [7].

^f Ref. [32].

^g Ref. [33].

^h Ref. [34]. ⁱ Ref. [35].

^j Ref. [36].

method [13–15] implemented in WIEN2k [16] package, is used to calculate the electronic and magnetic structures of a series of $Fe_{3-x}Mn_xZ$ (Z=Al, Ge, Sb) compounds. The electronic exchangecorrelation energy is treated using the generalized gradient approximation parameterized by Perdew–Burke–Ernzerhof (GGA-PBE) [17,18]. The total energy dependence on the cell volume is fitted to the Murnaghan equation of state (EOS) [19] by

$$E_{tot}(V) = \frac{B_0 V}{\dot{B}_0(\dot{B}_0 - 1)} \left[\left(\frac{V_0}{V} \right)^{\dot{B}_0} + \dot{B}_0 \left(1 - \frac{V_0}{V} \right) - 1 \right] + E_0, \tag{1}$$

where B_0 is the bulk modulus, \dot{B}_0 is the bulk modulus derivative and V_0 is the equilibrium volume.

By assuming the muffin-tin model for the crystal potential, the spherical harmonic expansion is used inside the muffin-tin sphere, and the plane-wave basis set is chosen outside the sphere. The maximum value of angular momentum $l_{max} = 10$ is taken for the valence wavefunction expansion inside the atomic spheres, while the charge density is Fourier expanded up to $G_{max} = 14$ (a.u.)⁻¹. The plane-wave cut-off value $K_{max} \times R_{MT} = 8$ is used for the plane-wave expansion in the interstitial region of the unit cell, where R_{MT} denotes the smallest atomic sphere radius (muffin tin radius) and K_{max} gives the magnitude of the largest K vector in

Download English Version:

https://daneshyari.com/en/article/10709807

Download Persian Version:

https://daneshyari.com/article/10709807

Daneshyari.com